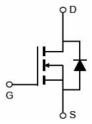
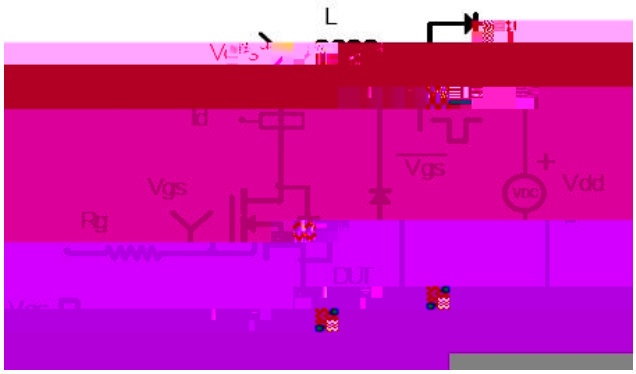
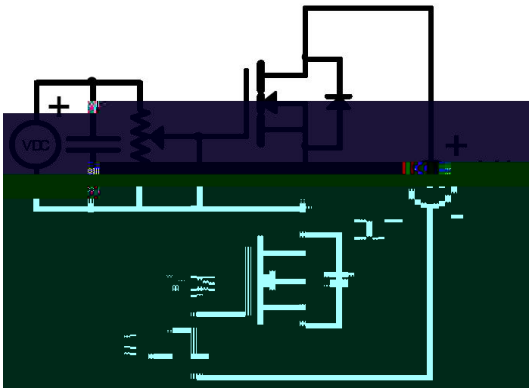
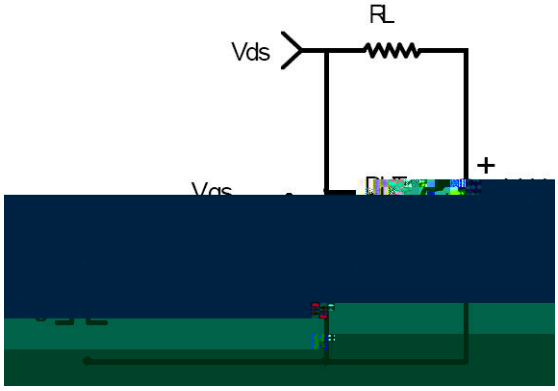
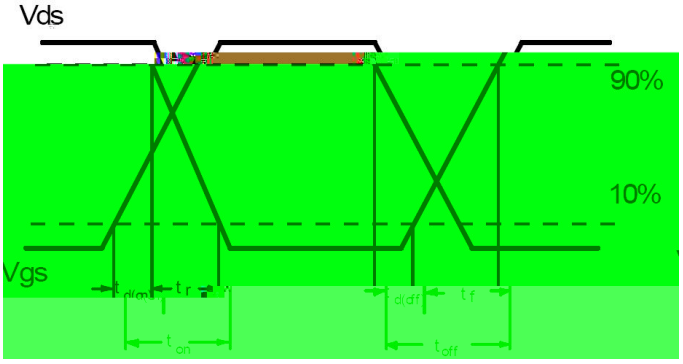
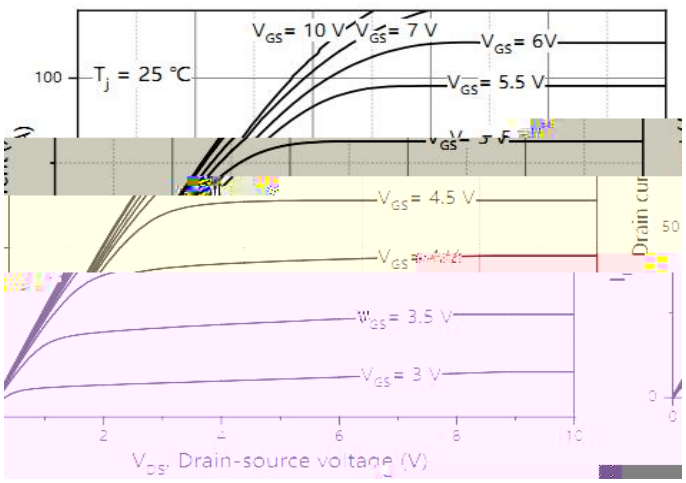
						 D G S

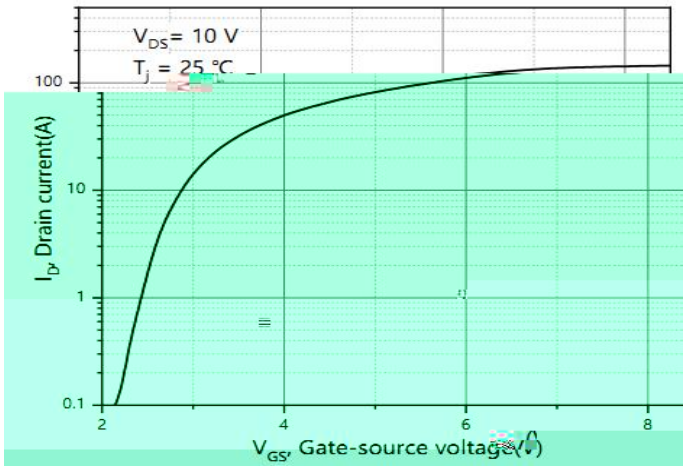

L
Vds
Id
Vgs
Vdd
Rg
DUT

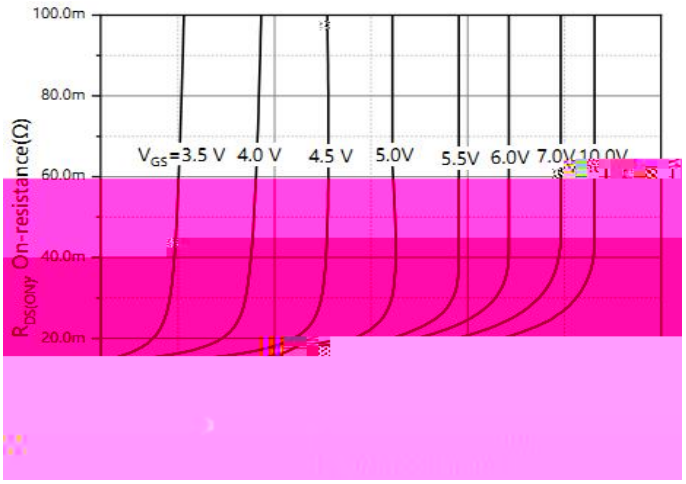

VDC

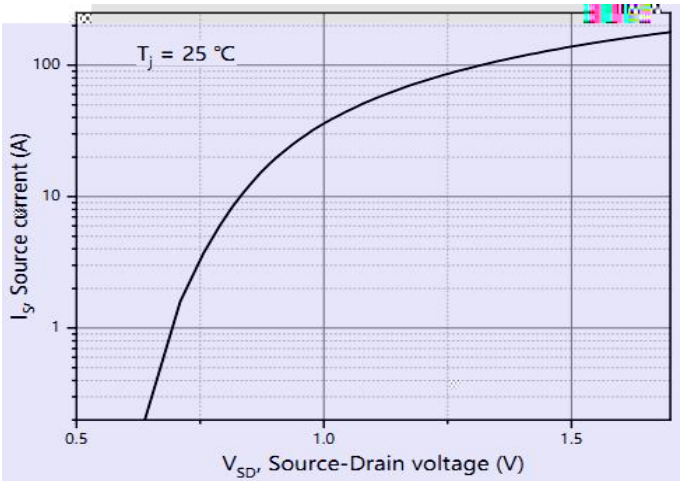

RL
Vds
Vgs

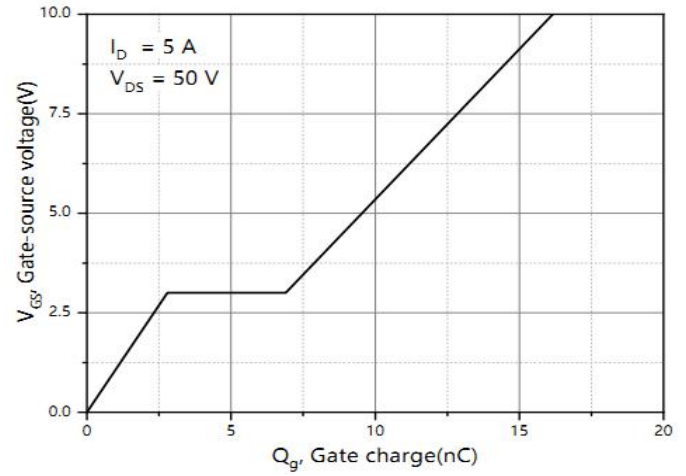

Vds
90%
10%
Vgs
tr
tf
ton
toff


V_{GS}= 10 V
V_{GS}= 7 V
V_{GS}= 6V
V_{GS}= 5.5 V
T_j = 25 °C
100
V_{GS}= 4.5 V
V_{GS}= 3.5 V
V_{GS}= 3 V
2
4
6
8
10
V_{DS}, Drain-source voltage (V)

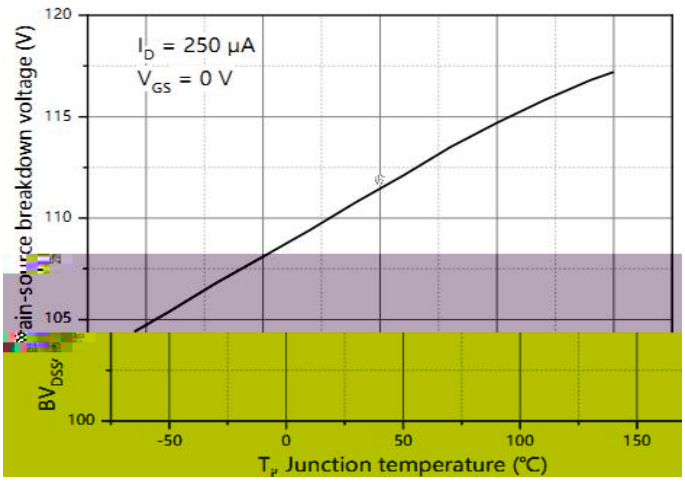

V_{DS}= 10 V
T_j = 25 °C
100
10
1
0.1
I_D, Drain current(A)
2
4
6
8
V_{GS}, Gate-source voltage(V)

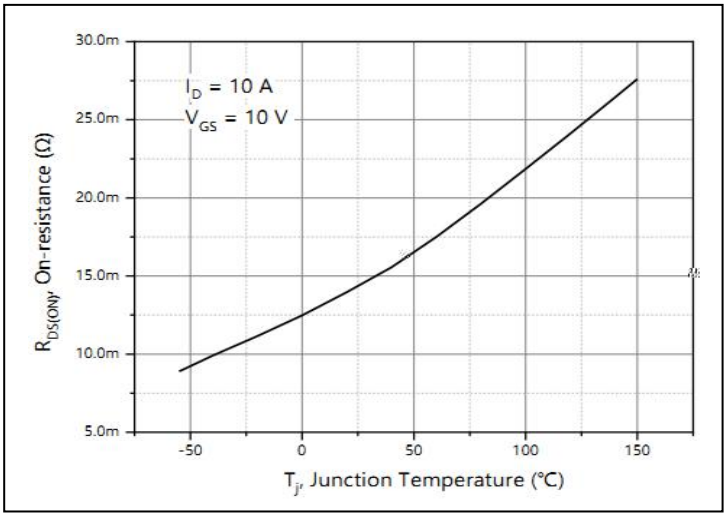

100.0m
80.0m
60.0m
40.0m
20.0m
$R_{DS(ON)}$, On-resistance(Ω)
V_{GS}=3.5 V
4.0 V
4.5 V
5.0V
5.5V
6.0V
7.0V
10.0V

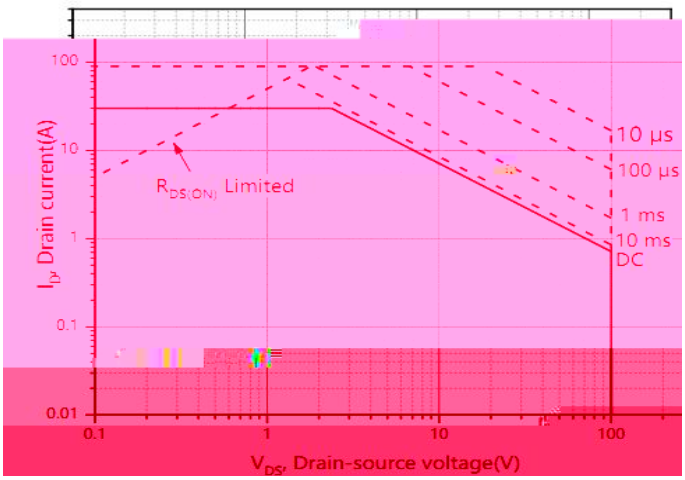

T_j = 25 °C
100
10
1
I_S, Source current (A)
0.5
1.0
1.5
V_{SD}, Source-Drain voltage (V)

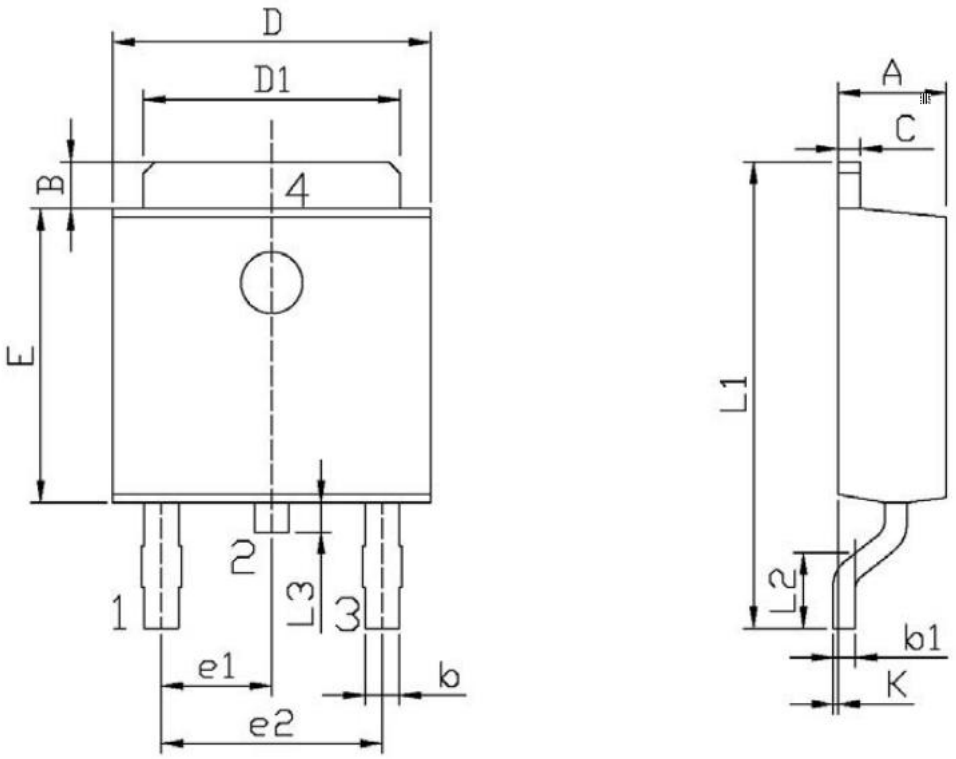

I_D = 5 A
V_{DS} = 50 V
10.0
7.5
5.0
2.5
0.0
V_{GS}, Gate-source voltage(V)
0
5
10
15
20
Q_g, Gate charge(nC)

32
28
24
20
16
12
8
4
I_D, Drain current (A)


I_D = 250 μA
V_{GS} = 0 V
BV_{DSS}, Drain-source breakdown voltage (V)
120
115
110
105
100
-50
0
50
100
150
T_j, Junction temperature (°C)


I_D = 10 A
V_{GS} = 10 V
$R_{DS(ON)}$, On-resistance (Ω)
30.0m
25.0m
20.0m
15.0m
10.0m
5.0m
-50
0
50
100
150
T_j, Junction Temperature (°C)


I_D, Drain current(A)
100
10
1
0.1
0.01
$R_{DS(ON)}$ Limited
10 μs
100 μs
1 ms
10 ms
DC
0.1
1
10
100
V_{DS}, Drain-source voltage(V)



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	
[redacted]					
D1	5.10	5.50	K	0.00	0.10

SILIKRON

Дневник

СИНОПТИК